

In the Claims

Claims 1-6 (canceled).

Claim 7 (currently amended): A method of forming a semiconductor construction, comprising:

forming a first semiconductor substrate comprising a first monocrystalline base and having a first transistor supported on the first monocrystalline base; the first transistor having source/drain regions associated therewith; the first substrate also having an insulative material formed over the base and ~~silicon-containing~~ semiconductor-material-containing plugs extending through the insulative material and to the source/drain regions; the ~~silicon-containing~~ semiconductor-material-containing plugs being separated from one another by the insulative material and defining a planarized upper surface above the first monocrystalline base;

providing a second semiconductor substrate comprising a second monocrystalline base and bonding the second semiconductor substrate to the ~~silicon-containing~~ semiconductor-material-containing plugs at the planarized upper surface above the first monocrystalline base; and

forming a second transistor supported over the second substrate.

Claim 8 (original): The method of claim 7 wherein one of the first and second transistors is a PMOS transistor and wherein the other of the first and second transistors is an NMOS transistor.

Claim 9 (original): The method of claim 7 wherein the second transistor comprises source/drain regions which extend entirely through the second monocrystalline base.

Claim 10 (original): The method of claim 7 wherein the second transistor comprises source/drain regions which extend only partially through the second monocrystalline base.

Claims 11-20 (cancelled).

Claim 21 (currently amended): A method of forming a semiconductor construction, comprising:

forming a first substrate comprising ~~silicon-containing~~ semiconductor-material-containing structures separated from one another by an insulative material; the ~~silicon-containing~~ semiconductor-material-containing structures defining an upper surface;

bonding a second semiconductor substrate to the ~~silicon-containing~~ semiconductor-material-containing structures at the upper surface; the second semiconductor substrate comprising a monocrystalline material which is bonded to the ~~silicon-containing~~ semiconductor-material-containing structures; and

forming at least one doped ~~silicon~~ semiconductor-material-containing region extending through the monocrystalline material and electrically contacting at least one of the ~~silicon-containing~~ semiconductor-material-containing structures.

Claim 22 (currently amended): The method of claim 21 wherein the forming the at least one doped ~~silicon~~ semiconductor-material-containing region comprises implanting dopant into the monocrystalline material.

Claim 23 (original): The method of claim 21 further comprising forming at least one insulative region extending at least partially into the monocrystalline material.

Claim 24 (original): The method of claim 21 further comprising forming at least one insulative region extending through the monocrystalline material.

Claim 25 (original): The method of claim 24 wherein the forming the at least one insulative region comprises:

forming an opening through the monocrystalline material; and
filling the opening with an insulative material.

Claim 26 (currently amended): The method of claim 21 wherein the forming the at least one doped ~~silicon~~ semiconductor-material-containing region comprises:

forming an opening through the monocrystalline material; and
filling the opening with a doped ~~silicon~~ semiconductor material.

Claim 27 (currently amended): The method of claim 26 wherein the doped ~~silicon~~ semiconductor material comprises doped amorphous silicon.

Claim 28 (currently amended): The method of claim 26 wherein the doped ~~silicon~~ semiconductor material comprises doped polycrystalline silicon.

Claim 29 (currently amended): The method of claim 21 further comprising forming at least one second doped ~~silicon~~ semiconductor-material-containing region within the second monocrystalline base and which does not extend entirely through the second monocrystalline base.

Claim 30 (currently amended): The method of claim 29 wherein the forming the at least one doped ~~silicon~~ semiconductor-material-containing region comprises:

forming an opening through the monocrystalline material; and
filling the opening with a doped ~~silicon~~ semiconductor material.

Claim 31 (currently amended): The method of claim 30 wherein the doped ~~silicon~~ semiconductor material comprises doped amorphous silicon.

Claim 32 (currently amended): The method of claim 30 wherein the doped ~~silicon~~ semiconductor material comprises doped polycrystalline silicon.

Claims 33-49 (cancelled).